



March 22, 2004

To: Commissioner for Patents  
P.O.Box 1450  
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572  
28 Davis Avenue  
Poughkeepsie, N.Y. 12603

Subject: | Serial No. 10/754,835 01/09/04 |  
Min-Hsiung Chiang  
METHOD TO REDUCE A CAPACITOR  
DEPLETION PHENOMENA  
| \_\_\_\_\_ |

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation  
In An Application.

The following Patents and/or Publications are submitted to  
comply with the duty of disclosure under CFR 1.97-1.99 and  
37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being  
deposited with the United States Postal Service as first class  
mail in an envelope addressed to: Commissioner for Patents,  
P.O. Box 1450, Alexandria, VA 22313-1450, on March 25, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date Stephen B. Ackerman 3/25/04


U.S. Patent 6,661,043 to Huang et al., "One-Transistor RAM Approach for High Density Memory Application," discusses a new method for the creation of a 1T RAM cell.

U.S. Patent 6,555,430 to Chudzik et al., "Process Flow for Capacitance Enhancement in a DRAM Trench," discusses methods forming a trench region of a trench capacitor structure having increase surface area.

U.S. Patent 6,420,226 to Chen et al., "Method of Defining a Buried Stack Capacitor Structure for a One Transistor RAM Cell," discloses a process for fabricating a buried stack capacitor structure, to be used in a one transistor, RAM cell.

U.S. Patent Application Publication US 2002/0094697 A1 to Leung et al., "DRAM Cell having a Capacitor Structure Fabricated Partially in a Cavity and Method for Operating Same," discusses a memory system that includes a dynamic random access memory (DRAM) cell including an access transistor and a capacitor structure fabricated in a semiconductor substrate.

Sincerely,

A handwritten signature in black ink, appearing to read "Stephen B. Ackerman", with a stylized flourish at the end.

Stephen B. Ackerman,  
Reg. No. 37761

MAR 29 2004

(Use several sheets if necessary)

License Number

$$10 \overline{) 754.835}$$

Lyndal

min-Hsiang Chian

Final Date

01/09/04

Grades 2-4 Unit

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	US Patent App. Publication US 2002/0094697 A1 to
	Leung et al., Pub. Date 7/18/02, US Class 438/766,
	filed 11/2/01.

DATE COMPLETED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.